

NDT02N60Z

N-Channel Power MOSFET 600 V, 8.0 Ω

Features

- 100% Avalanche Tested
- Extremely High dv/dt Capability
- Gate Charge Minimized
- Zener-protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	600	V
Gate-to-Source Voltage	V _{GS}	±30	V
Continuous Drain Current R _{θJA} Steady State, T _C = 25°C	I _D	0.3	A
Continuous Drain Current R _{θJA} Steady State, T _C = 100°C	I _D	0.21	A
Power Dissipation – R _{θJA} Steady State, T _C = 25°C	P _D	2.0	W
Pulsed Drain Current	I _{DM}	5	A
Continuous Source Current (Body Diode)	I _S	2.2	A
Single Pulse Drain-to-Source Avalanche Energy (I _D = 1.4 A)	EAS	38	mJ
Peak Diode Recovery (Note 1)	dV/dt	4.5	V/ns
Maximum Temperature for Soldering Leads	T _L	260	°C
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_S < 2.2 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, T_J = +150°C

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Ambient Steady State NDT02N60Z (Note 2) NDT02N60Z (Note 3)	R _{θJA}	61 148	°C/W

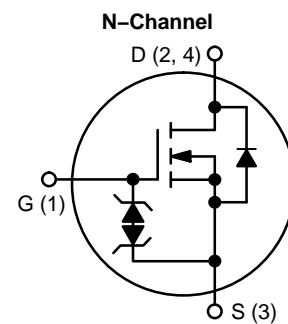
2. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127" sq. [2 oz] including traces)
3. Surface-mounted on FR4 board using minimum recommended pad size (Cu area = 0.026" sq. [2 oz]).



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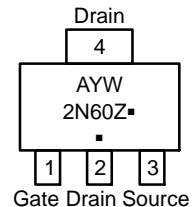
V _{(BR)DSS}	R _{DS(ON)} MAX
600 V	8.0 Ω @ 10 V



MARKING DIAGRAM



SOT-223
CASE 318E
STYLE 3



- A = Assembly Location
- Y = Year
- W = Work Week
- 2N60Z = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NDT02N60Z

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	600			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	Reference to 25°C, I _D = 1 mA		605		mV/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	T _J = 25°C		1	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V			±10	μA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 50 μA	3.0	3.9	4.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	Reference to 25°C, I _D = 50 μA		10.2		mV/°C
Static Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.7 A		5.9	8.0	Ω
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 0.7 A		1.3		S

DYNAMIC CHARACTERISTICS

Input Capacitance (Note 5)	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		170		pF
Output Capacitance (Note 5)	C _{oss}			22		
Reverse Transfer Capacitance (Note 5)	C _{rss}			4.8		
Effective output capacitance, energy related (Note 7)	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 to 480 V		7.8		
Effective output capacitance, time related (Note 8)	C _{o(tr)}	I _D = constant, V _{GS} = 0 V, V _{DS} = 0 to 480 V		12.4		
Total Gate Charge (Note 5)	Q _g	V _{DS} = 300 V, I _D = 1.6 A, V _{GS} = 10 V		7.4		nC
Gate-to-Source Charge (Note 5)	Q _{gs}			1.8		
Gate-to-Drain ("Miller") Charge (Note 5)	Q _{gd}			3.8		
Plateau Voltage	V _{GP}			6.4		V
Gate Resistance	R _g			11.5		Ω

RESISTIVE SWITCHING CHARACTERISTICS (Note 6)

Turn-on Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 1.6 A, V _{GS} = 10 V, R _G = 0 Ω		10		ns
Rise Time	t _r			6		
Turn-off Delay Time	t _{d(off)}			14		
Fall Time	t _f			8		

SOURCE-DRAIN DIODE CHARACTERISTICS

Diode Forward Voltage	V _{SD}	I _S = 1.6 A, V _{GS} = 0 V	T _J = 25°C		0.9	1.2	V
			T _J = 100°C		0.8		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V, I _S = 1.6 A, dI/dt = 100 A/μs		230		ns	
Charge Time	t _a			50			
Discharge Time	t _b			180			
Reverse Recovery Charge	Q _{rr}			495			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

5. Guaranteed by design.

6. Switching characteristics are independent of operating junction temperatures.

7. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

8. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

TYPICAL CHARACTERISTICS

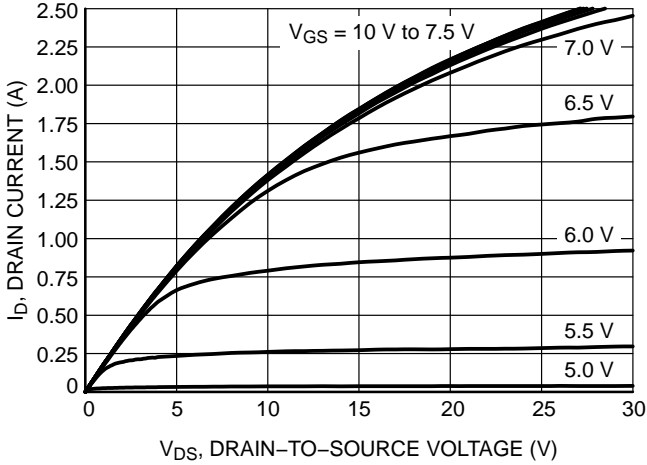


Figure 1. On-Region Characteristics

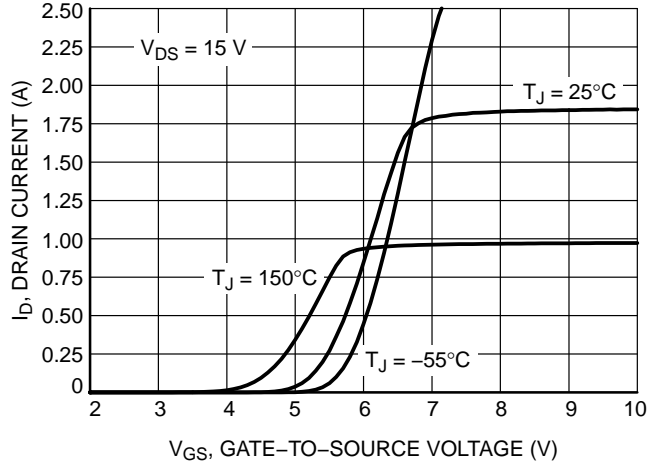


Figure 2. Transfer Characteristics

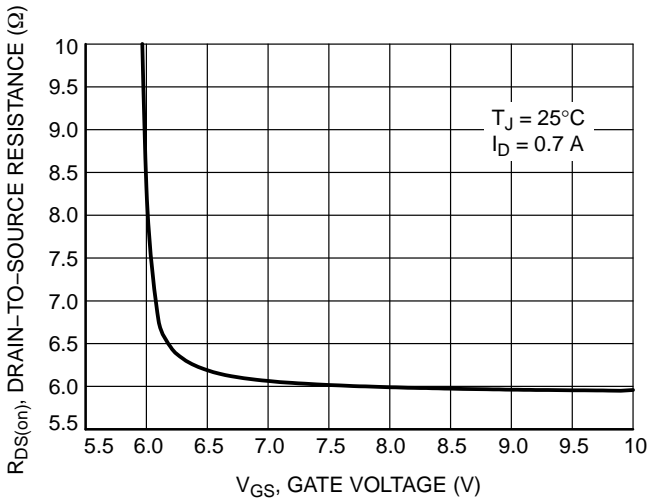


Figure 3. On-Resistance vs. Gate-to-Source Voltage

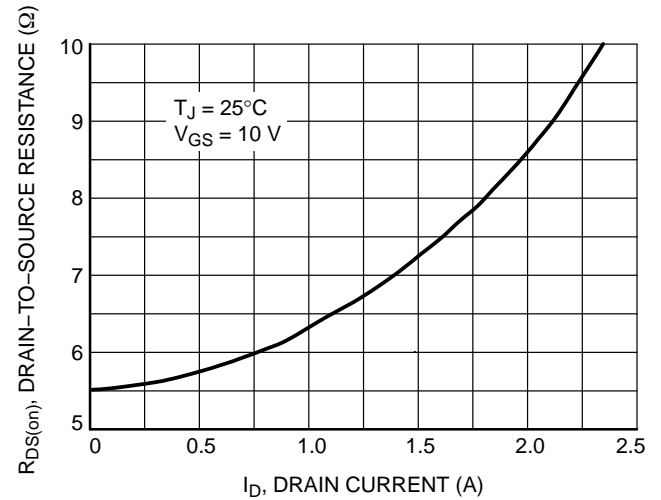


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

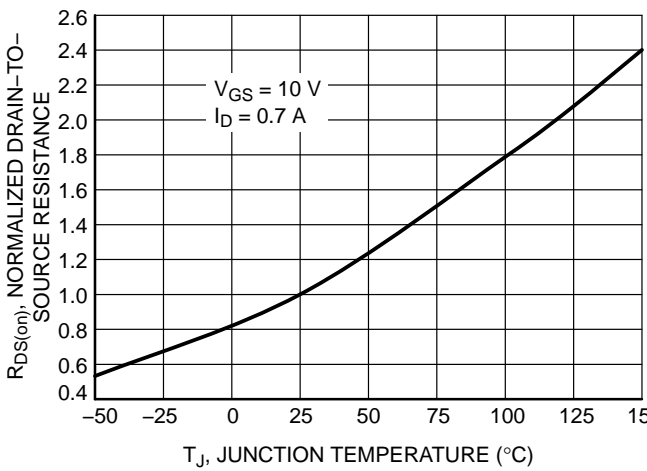


Figure 5. On-Resistance Variation with Temperature

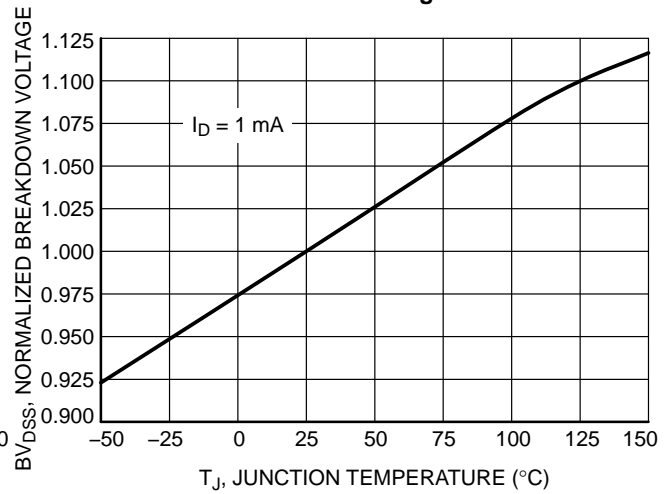


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

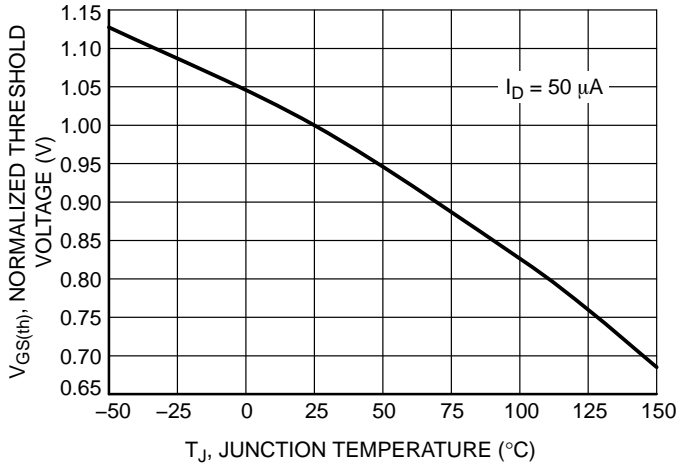


Figure 7. Threshold Voltage Variation with Temperature

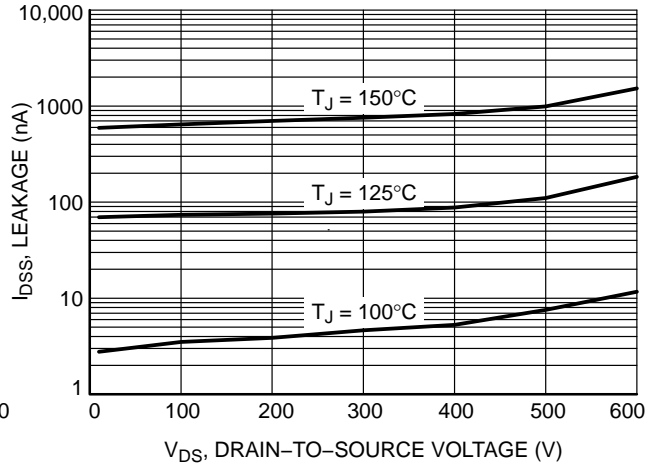


Figure 8. Drain-to-Source Leakage Current vs. Voltage

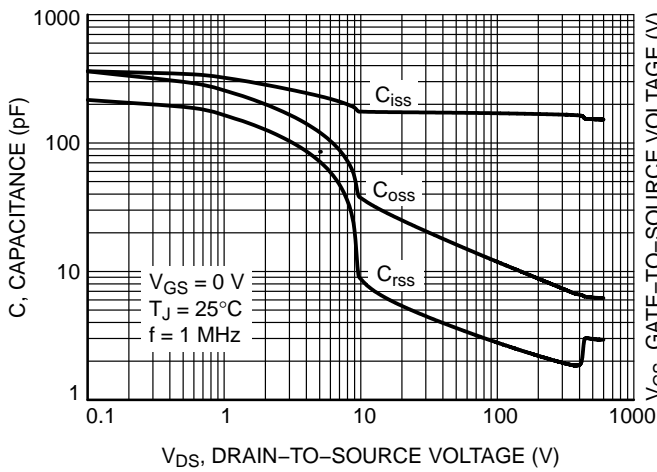


Figure 9. Capacitance Variation

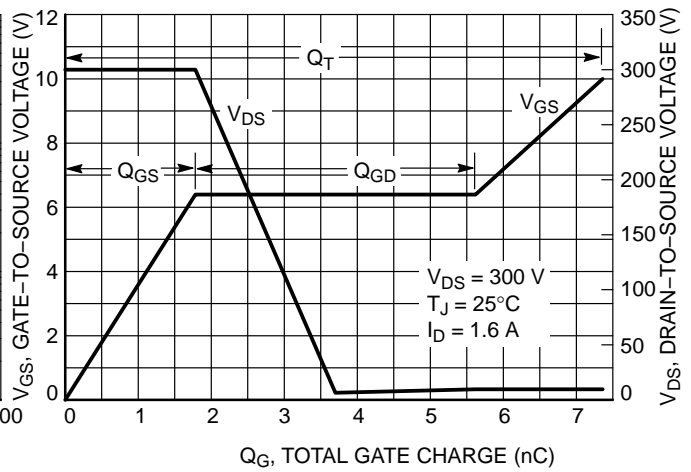


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

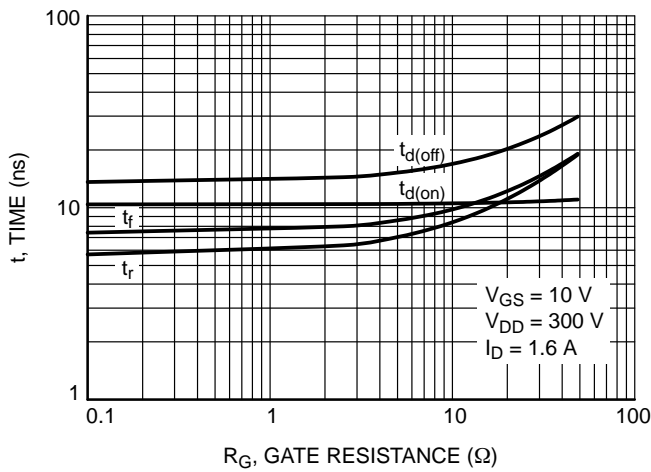


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

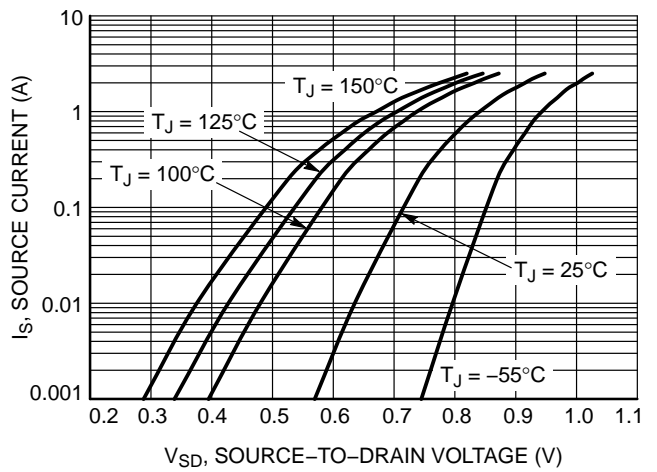


Figure 12. Diode Forward Voltage vs. Current

NDT02N60Z

TYPICAL CHARACTERISTICS

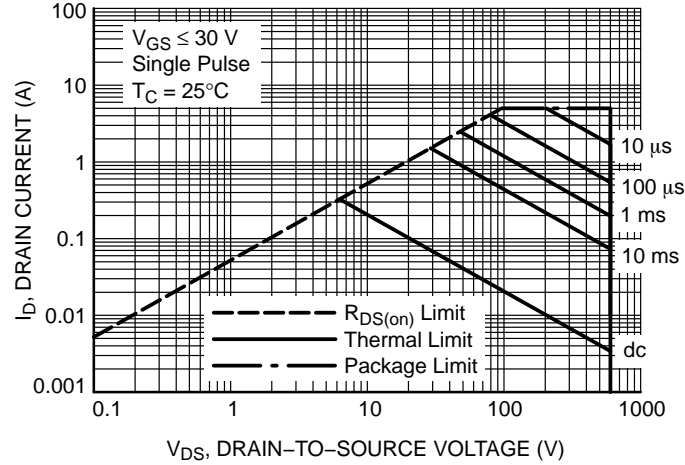


Figure 13. Maximum Rated Forward Biased Safe Operating Area

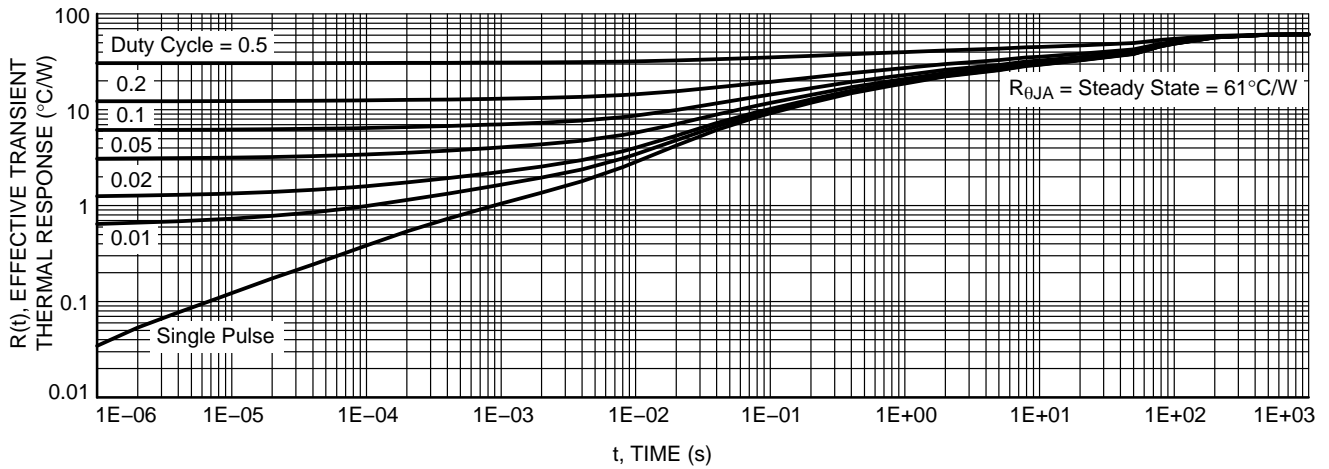


Figure 14. Thermal Impedance (Junction-to-Ambient)

ORDERING INFORMATION

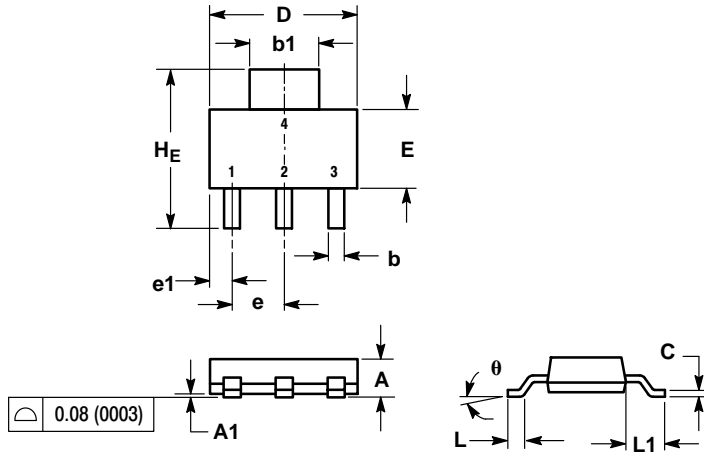
Device	Package	Shipping†
NDT02N60ZT1G	SOT-223 (Pb-Free, Halogen Free)	1000 / Tape & Reel
NDT02N60ZT3G		4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NDT02N60Z

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE N



NOTES:

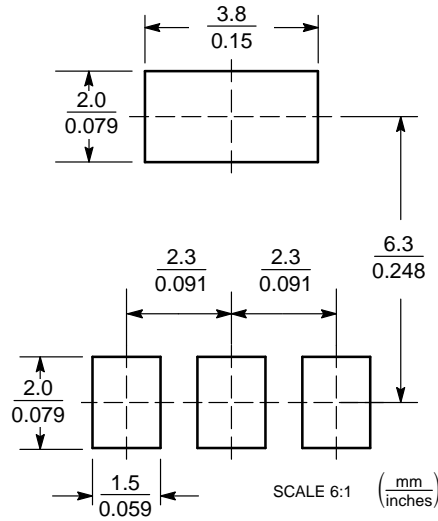
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	---	10°	0°	---	10°

STYLE 3:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

SOLDERING FOOTPRINT



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